

ABSTRACT OF THE DISCLOSURE

A semiconductor light emitting device comprises:
a substrate; an n-type layer provided on the substrate
5 and made of a nitride semiconductor material; a multiple
quantum well structure active layer including a plurality
of well layers each made of $\text{In}_x\text{Ga}_{(1-x-y)}\text{Al}_y\text{N}$ ($0 \leq x$, $0 \leq y$, $x+y < 1$)
and a plurality of barrier layers each made of $\text{In}_s\text{Ga}_{(1-s-t)}\text{Al}_t\text{N}$ ($0 \leq s$, $0 \leq t$, $s+t < 1$), the multiple quantum well
10 structure active layer being provided on the n-type layer;
and a p-type layer provided on the multiple quantum well
structure active layer and made of a nitride semiconductor
material. The p-type layer contains hydrogen, and the
hydrogen concentration of the p-type layer is greater than
15 or equal to about 1×10^{16} atoms/cm³ and less than or equal
to about 1×10^{19} atoms/cm³.